

## P-Channel 30-V (D-S) MOSFET

### ■ FEATURES

- Low  $R_{DS(on)}$  Provides Higher Efficiency and Extends Battery Life
- High power and current handling capability
- Miniature SOP-8 Surface Mount Package Saves Board Space

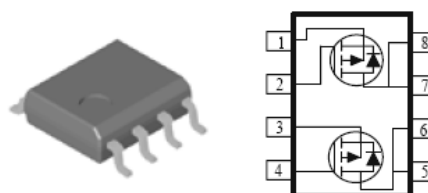
### ■ Product Summary

| MOSFET      |                        |           |
|-------------|------------------------|-----------|
| $V_{DS}(V)$ | $R_{DS(on)} (m\Omega)$ | $I_D (A)$ |
| -30         | 60 @ $V_{GS} = -10V$   | -4.9      |
|             | 90 @ $V_{GS} = -4.5V$  | -3.7      |

### ■ Description

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $R_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, and PCMCIA cards, cellular and cordless telephones.

### ■ SOP-8



### Maximum Ratings (TA = 25 °C UNLESS OTHERWISE NOTED)

| Symbol         | Parameter                                                 |                    | Maximum    | Unit |
|----------------|-----------------------------------------------------------|--------------------|------------|------|
| $V_{DS}$       | Drain-Source Voltage                                      |                    | -30        | V    |
| $V_{GS}$       | Gate-Source Voltage                                       |                    | ±20        |      |
| $I_D$          | Continuous Drain Current <sup>a</sup>                     | $T_A = 25^\circ C$ | ±4.9       | A    |
|                |                                                           | $T_A = 70^\circ C$ | ±4.2       |      |
| $I_{DM}$       | Pulsed Drain Current <sup>b</sup>                         |                    | ±30        |      |
| $I_S$          | Continuous Source Current (Diode Conduction) <sup>a</sup> |                    | -1.6       | A    |
| $P_D$          | Power Dissipation <sup>a</sup>                            | $T_A = 25^\circ C$ | 2.1        | W    |
|                |                                                           | $T_A = 70^\circ C$ | 1.3        |      |
| $T_J, T_{stg}$ | Operation Junction and Storage Temperature Range          |                    | -55 to 150 | °C   |

### Thermal Resistance Ratings

| Symbol          | Parameter                                |                         | Maximum | Unit |
|-----------------|------------------------------------------|-------------------------|---------|------|
| $R_{\theta JA}$ | Maximum Junction-to-Ambient <sup>a</sup> | $t \leq 10 \text{ sec}$ | 60      | °C/W |
| $R_{\theta JC}$ | Maximum Junction-to-Case <sup>a</sup>    | $t \leq 5 \text{ sec}$  | 40      | °C/W |

#### Notes:

- (a) Surface Mounted on 1" x 1" FR4 Board.  
(b) Pulse width limited by maximum junction temperature

**Electrical Characteristics**

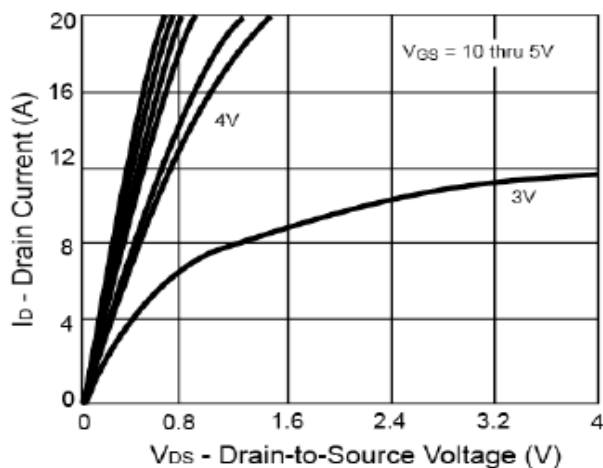
| SPECIFICATIONS (TA = 25°C UNLESS OTHERWISE NOTED) |                     |                                                                                                                   |        |      |      |      |
|---------------------------------------------------|---------------------|-------------------------------------------------------------------------------------------------------------------|--------|------|------|------|
| Parameter                                         | Symbol              | Test Condition                                                                                                    | Limits |      |      | Unit |
|                                                   |                     |                                                                                                                   | Min    | Typ  | Max  |      |
| Static                                            |                     |                                                                                                                   |        |      |      |      |
| Gate-Threshold Voltage                            | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>b</sub> = -250 uA                                                      | -1     | -1.5 | -3   | V    |
| Gate-Body Leakage                                 | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> =±20V                                                                      |        |      | ±100 | nA   |
| Zero Gate Voltage Drain Current                   | I <sub>DSS</sub>    | V <sub>DS</sub> = -24 V, V <sub>GS</sub> = 0 V                                                                    |        |      | -1   | uA   |
|                                                   |                     | V <sub>DS</sub> = -24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C                                             |        |      | -5   |      |
| On-State Drain Current <sup>a</sup>               | I <sub>D(on)</sub>  | V <sub>DS</sub> = -5V, V <sub>GS</sub> =-10V                                                                      | -30    |      |      | A    |
| Drain-Source On-Resistance <sup>a</sup>           | R <sub>DS(on)</sub> | V <sub>GS</sub> = -10 V, I <sub>D</sub> = -4.9 A                                                                  |        | 50   | 60   | mΩ   |
|                                                   |                     | V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.7 A                                                                 |        | 75   | 90   |      |
| Forward Transconductance <sup>a</sup>             | g <sub>fs</sub>     | V <sub>DS</sub> = -15V, I <sub>D</sub> = -4.9A                                                                    |        | 10   |      | S    |
| Diode Forward Voltage                             | V <sub>SD</sub>     | I <sub>S</sub> = -1.9 A, V <sub>GS</sub> = 0 V                                                                    |        |      | -1.3 | V    |
| Dynamic <sup>b</sup>                              |                     |                                                                                                                   |        |      |      |      |
| Total Gate Charge                                 | Q <sub>g</sub>      | V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V<br>I <sub>D</sub> = -5.2A                                          |        | 28   |      | nC   |
| Gate-Source Charge                                | Q <sub>gs</sub>     |                                                                                                                   |        | 3    |      |      |
| Gate-Drain Charge                                 | Q <sub>gd</sub>     |                                                                                                                   |        | 7    |      |      |
| Input Capacitance                                 | C <sub>iss</sub>    | V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V<br>f=1MHz                                                            |        | 745  |      | pF   |
| Output Capacitance                                | C <sub>oss</sub>    |                                                                                                                   |        | 440  |      |      |
| Reverse Transfer Capacitance                      | C <sub>rss</sub>    |                                                                                                                   |        | 120  |      |      |
| Switching                                         |                     |                                                                                                                   |        |      |      |      |
| Turn-On Delay Time                                | t <sub>d(on)</sub>  | V <sub>DD</sub> =-15V, R <sub>L</sub> = 15Ω I <sub>D</sub> = -1A,<br>V <sub>GEN</sub> = -10V, R <sub>G</sub> = 6Ω |        | 9    |      | nS   |
| Turn-On Rise Time                                 | t <sub>r</sub>      |                                                                                                                   |        | 15   |      |      |
| Turn-Off Delay Time                               | t <sub>d(off)</sub> |                                                                                                                   |        | 75   |      |      |
| Turn-Off Fall Time                                | t <sub>f</sub>      |                                                                                                                   |        | 40   |      |      |

**Notes:**

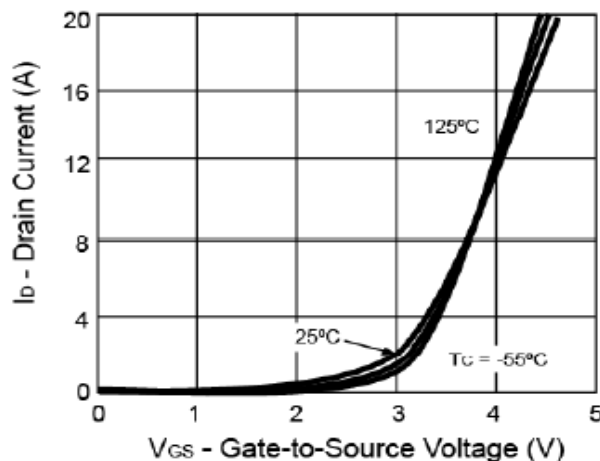
- (a) Pulse test: pulse width  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$   
(b) Guaranteed by design; not subject to production testing

## Typical Electrical Characteristics

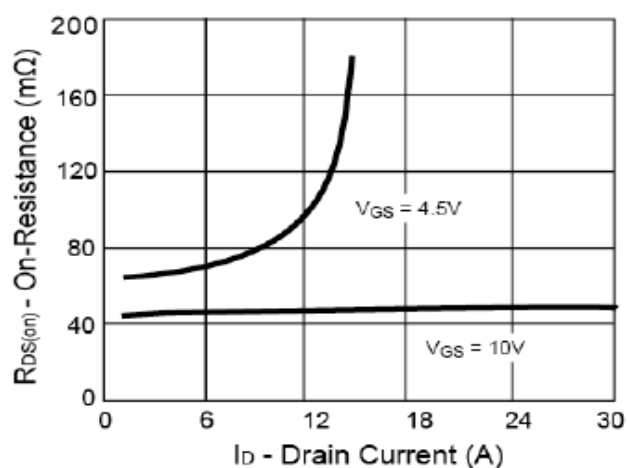
### Output Characteristics



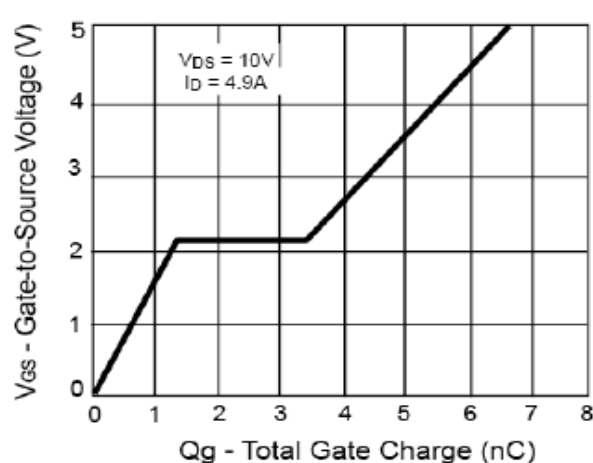
### Transfer Characteristics



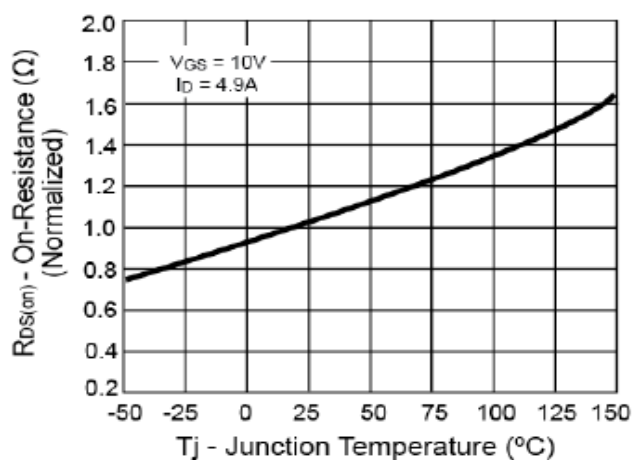
### On-Resistance vs. Drain Current



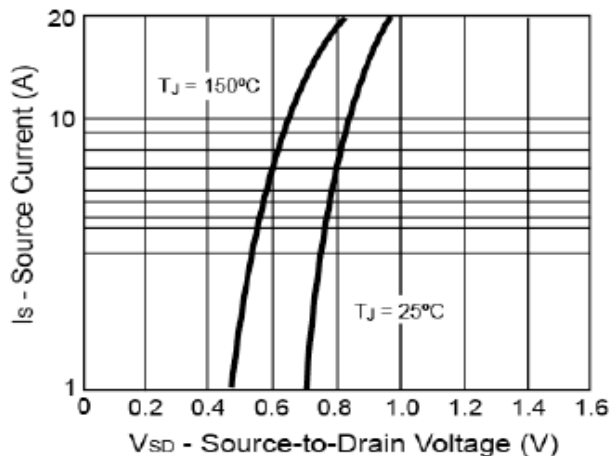
### Gate Charge



### On-Resistance vs. Junction Temperature

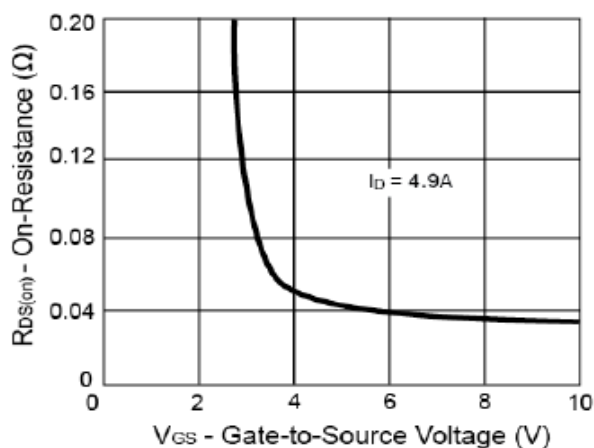


### Source-Drain Diode Forward Voltage

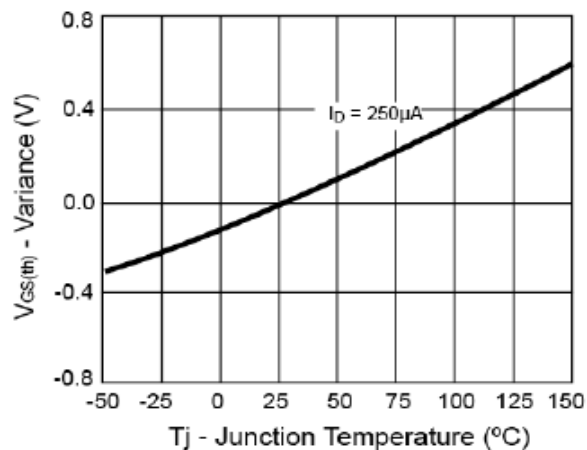


## Typical Electrical Characteristics

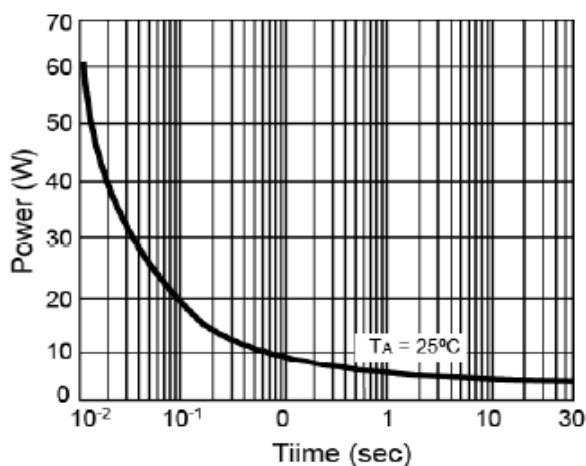
On-Resistance vs. Gate-Source Voltage



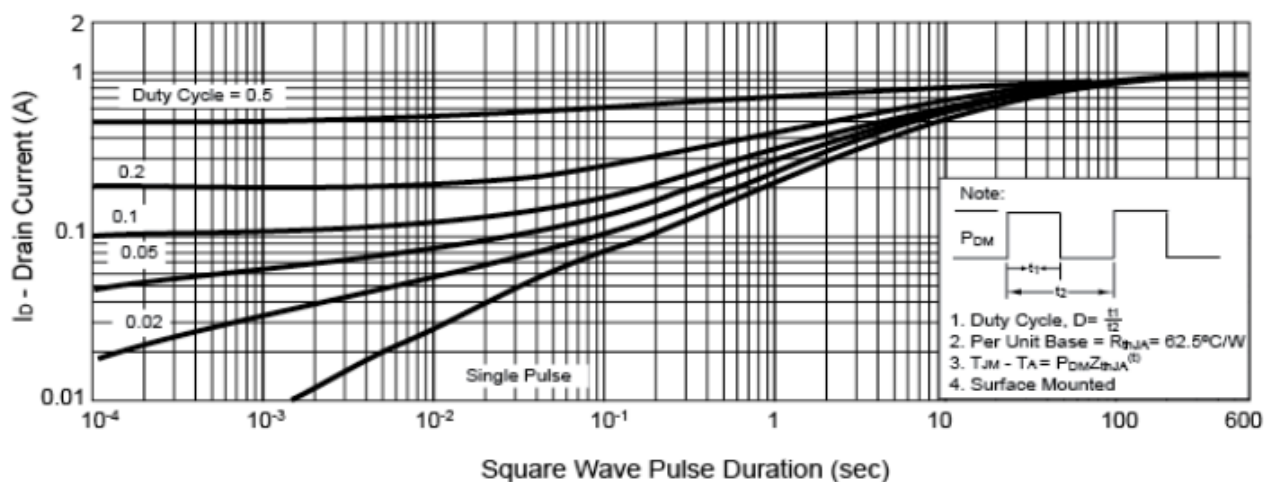
Threshold Voltage



Single Pulse Power

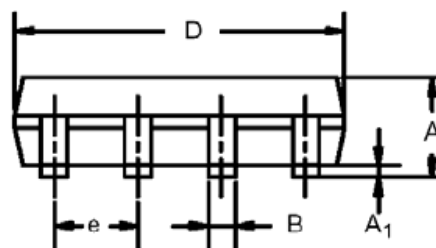
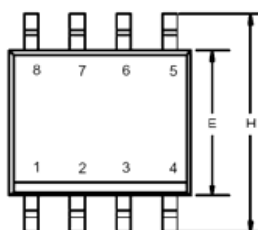


Normalized Thermal Transient Impedance, Junction-to-Ambient

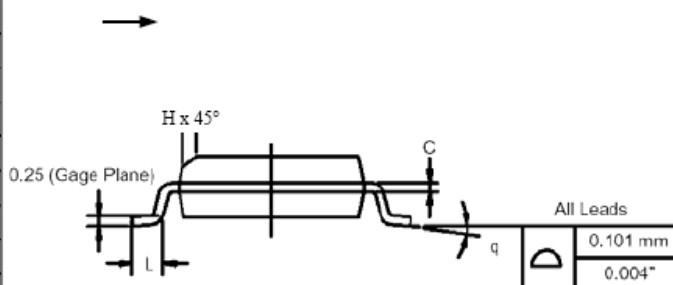


## Package Information

### SOP-8 : 8LEAD



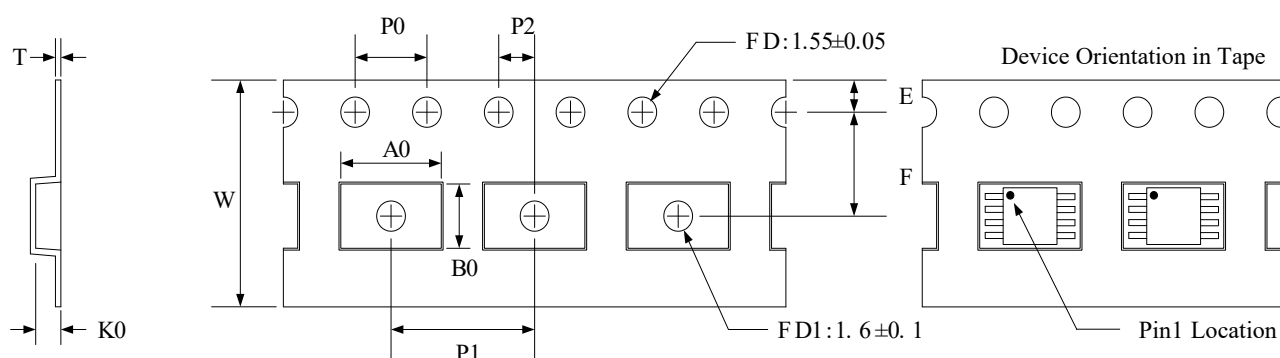
| Dim            | MILLIMETERS |      | INCHES    |       |
|----------------|-------------|------|-----------|-------|
|                | Min         | Max  | Min       | Max   |
| A              | 1.35        | 1.75 | 0.053     | 0.069 |
| A <sub>1</sub> | 0.10        | 0.20 | 0.004     | 0.008 |
| B              | 0.35        | 0.51 | 0.014     | 0.020 |
| C              | 0.19        | 0.25 | 0.0075    | 0.010 |
| D              | 4.80        | 5.00 | 0.189     | 0.196 |
| E              | 3.80        | 4.00 | 0.150     | 0.157 |
| e              | 1.27 BSC    |      | 0.050 BSC |       |
| H              | 5.80        | 6.20 | 0.228     | 0.244 |
| h              | 0.25        | 0.50 | 0.010     | 0.020 |
| L              | 0.50        | 0.93 | 0.020     | 0.037 |
| q              | 0°          | 8°   | 0°        | 8°    |



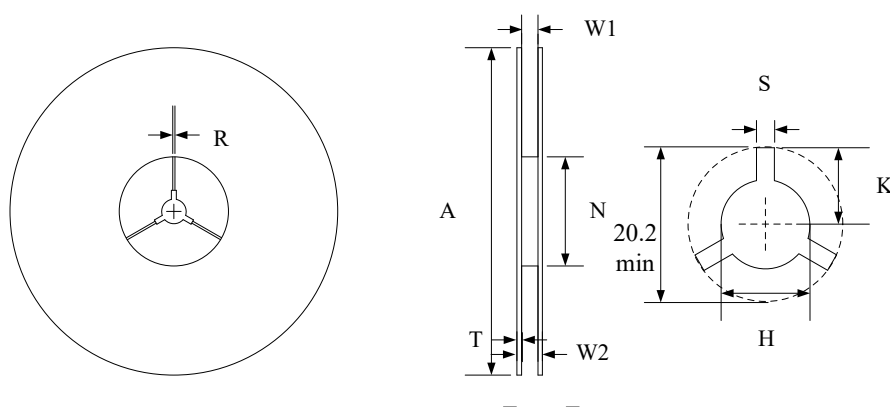
## Ordering Information

| Part Number | Working Voltage | Quantity Per Reel | Reel Size |
|-------------|-----------------|-------------------|-----------|
| 4953        | 30 V            | 3,000             | 13 Inch   |

## Tape and Reel Specification



| Symbol          | W         | A0       | B0      | K0       | E        | F        | P1       | P0      | P2      | T        |
|-----------------|-----------|----------|---------|----------|----------|----------|----------|---------|---------|----------|
| Dimensions (mm) | 12.00±0.3 | 6.40±0.1 | 5.2±0.1 | 2.10±0.1 | 1.75±0.1 | 5.50±0.1 | 8.00±0.1 | 4.0±0.1 | 2.0±0.1 | 0.3±0.05 |



| Symbol          | Reel Size | A         | N         | W2       | W1               | H                | T       | S       | K        | R       |
|-----------------|-----------|-----------|-----------|----------|------------------|------------------|---------|---------|----------|---------|
| Dimensions (mm) | Φ330      | 330.0±2.0 | 100.0±2.0 | 18.4 max | 12.4+2.0<br>-0.0 | 13.0+0.5<br>-0.2 | 2.0±0.2 | 1.5 min | 10.1 min | 2.5 min |